L Number	Hits	Search Text	DB	Time stamp
- Mannet	2	("6348705").PN.	USPAT; US-PGPUB; EPO; JPO;	2002/09/16 08:11
_	13687	@ad<=20010508 and 'high dielectric constant'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/16 08:31
_	132	(@ad<=20010508 and 'high dielectric constant') and 'conductive barrier'	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/01/29 14:24
-	119	((@ad<=20010508 and 'high dielectric constant') and 'conductive barrier') and Al	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/16 08:24
_	77	((@ad<=20010508 and 'high dielectric constant') and 'conductive barrier') and Aluminum	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/16 08:25
-	3291	@ad<=20010508 and 'BST'	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/09/16 08:33
	79	(@ad<=20010508 and 'BST') and 'TiAlN'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/01/29 13:41
	39	((@ad<=20010508 and 'BST') and 'TiAlN') and aluminum	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/01 06:54
-	6626	((257/295-296) or (257/751) or (257/310) or (438/3) or (257/763-764) or (257/303) or (257/306)).CCLS.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/16 11:37
-	24	(((257/295-296) or (257/751) or (257/310) or (438/3) or (257/763-764) or (257/303) or (257/306)).CCLS.) and @ad<=20010508 and 'BST' and 'TiAlN' and 'metal layer'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/16 12:52
_	29173	@ad<=20010508 and 'ferroelectric'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/16 12:05
_	30	(@ad<=20010508 and 'ferroelectric') and 'BST' and 'TiAlN' and 'metal layer'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/30 07:15
-	29	(@ad<=20010508 and 'ferroelectric') and 'BST' and 'TiAlN' and 'aluminum'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/16 13:26
_	20	(@ad<=20010508 and 'ferroelectric') and 'capacitor' with 'BST' and 'TiAlN' and 'aluminum'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/16 13:26

_	25	@ad<=20010508 and 'perovskite BST' or	USPAT;	2002/09/16
		'amorphous BST'	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	15:09
_	3	@ad<=20010508 and 'amorphous BST' and conductive adj barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/02 13:06
_	569	(257/310).CCLS.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/09/16 15:41
-	532	((257/310).CCLS.) and @ad<=20010508	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/01/29 13:56
	11	(@ad<=20010508 and 'ferroelectric') and 'BST' and 'barrier' and 'aluminum layer'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/09/16 15:45
_	270	@ad<=19991222 and 'conductive barrier' and 'TiN'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/05/12 12:52
_	566	((257/310).CCLS.) and @ad<=20010508	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/01/29 14:05
_	43	<pre>@ad<=19991222 and 'conductive barrier' and 'TiN' and 'BST'</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/01/29 14:05
	6	<pre>@ad<=19991222 and 'conductive barrier' and 'TiN' and 'BST' and 'copper'</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/29 15:02
	2342	@ad<=19991222 and (257/295-296).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/29 14:15
-	795	@ad<=19991222 and (257/751).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/01/29 14:09
_	1232	@ad<=19991222 and (257/763-764).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/01/29 14:10
_	372	@ad<=19991222 and (257/303).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/01/29 14:11
	1094	@ad<=19991222 and (257/306).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/29 14:12
1			IBM_TDB	

	479	@ad<=19991222 and (438/3).ccls.	USPAT;	2003/01/29
			US-PGPUB; EPO; JPO; DERWENT; IBM TDB	14:12
	1072	@ad<=19991222 and (438/439-440).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/29 14:13
_	687	@ad<=19991222 and (438/687-688).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/29 14:21
-	4	(("6294420") or ("6365517")).PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/29 14:21
_	38	<pre>@ad<=19991222 and 'high dielectric constant' and 'conductive barrier' and 'copper'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/01/29 14:26
_	21	<pre>@ad<=19991222 and 'conductive barrier' and 'TiN' and 'BST' and 'aluminum'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/29 15:02
_	29	@ad<=19991222 and 'ferroelectric' and 'TiAlN' and 'metal layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 08:54
-	8	@ad<=19991222 and 'capacitor' with 'ferroelectric' with 'conductive diffusion barrier'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/12 14:27
-	17	<pre>@ad<=19991222 and 'conductive barrier' and 'TiAlN'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/12 12:52
-	5	@ad<=19991222 and 'BST' and 'conductive barrier' with 'TiAlN'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/12 13:00
_	10	<pre>@ad<=19991222 and 'copper' and 'TiAlN' and 'BST'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/12 14:42
_	1	@ad<=19991222 and 'copper' same 'TiAlN' same 'BST'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/12 13:07
-	0	@ad<=19991222 and 'capacitor' with 'BST' with 'TiAlN'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/12 14:25
_	2	@ad<=19991222 and 'BST' with 'TiAlN'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 14:25

_	8	@ad<=19991222 and 'capacitor' with	USPAT;	2004/07/01
		'ferroelectric' with 'conductive diffusion barrier'	US-PGPUB; EPO; JPO;	07:04
		diffusion barrier	DERWENT;	
			IBM TDB	
_	0	@ad<=19991222 and copper near electrode	USPAT;	2003/05/12
	<u> </u>	and 'BST' same 'TiAlN'	US-PGPUB;	14:39
	1 1 1 1		EPO; JPO;	
			DERWENT;	
_	3	@ad<=19991222 and copper and 'BST' same	USPAT;	2003/05/12
		'TiAlN'	US-PGPUB;	14:39
			EPO; JPO;	
			DERWENT;	
	50	Gode-10001222 and INII and IMININI and	IBM_TDB USPAT;	2002/05/12
_	50	@ad<=19991222 and 'Al' and 'TiAlN' and 'BST'	US-PGPUB;	2003/05/12 14:46
			EPO; JPO;	11.10
			DERWENT;	
			IBM_TDB	
-	25	1 -	USPAT;	2004/07/02
		and 'BST'	US-PGPUB;	08:25
			EPO; JPO; DERWENT;	
			IBM TDB	
_	48	@ad<=19991222 and 'conductive' and	USPAT;	2003/05/12
		'TiAlN' and 'BST'	US-PGPUB;	14:58
			EPO; JPO;	
			DERWENT;	
_	15	@ad<=19991222 and 'stack capacitor' and	IBM_TDB USPAT;	2004/07/01
	15	'TiAlN' and 'BST'	US-PGPUB;	07:22
			EPO; JPO;	
	:	_	DERWENT;	
		#00000167006#	IBM_TDB	0000/10/15
_	2	"20020167086"	USPAT; US-PGPUB;	2003/10/15
			EPO; JPO;	12.33
			DERWENT;	
			IBM_TDB	
-	8	<pre>@ad<=20010508 and 'BST' same 'TiN' same</pre>	USPAT;	2004/07/01
		'aluminum' with 'copper'	US-PGPUB;	07:02
			EPO; JPO; DERWENT;	
			IBM TDB	
_	3	@ad<=20010508 and 'high k' same 'TiN'	USPAT;	2004/07/01
		same 'aluminum' with 'copper'	US-PGPUB;	07:03
			EPO; JPO;	
	1		DERWENT;	
_	2	("5990541").PN.	IBM_TDB USPAT;	2004/07/01
	_		US-PGPUB;	07:03
			EPO; JPO;	
			DERWENT;	
	_	0-4-10001000 1 15 1 1	IBM_TDB	2004/07/01
	5	<pre>@ad<=19991222 and 'ferroelectric' same 'barrier' same 'copper' with 'electrode'</pre>	USPAT; US-PGPUB;	2004/07/01 07:08
		patrier same copper with electrode	EPO; JPO;	07.00
	1		DERWENT;	
			IBM_TDB	
_	236		USPAT;	2004/07/01
		'barrier' same 'metal' with 'electrode'	US-PGPUB;	07:13
			EPO; JPO; DERWENT;	
	1		IBM TDB	
_	4	@ad<=19991222 and 'capacitor' same	USPAT;	2004/07/01
		'ferroelectric' same 'barrier' same	US-PGPUB;	07:09
		'copper' with 'electrode'	EPO; JPO;	
			DERWENT;	
			IBM TDB	

-	5	<pre>@ad<=19991222 and 'stack capacitor' and 'TiAlN' and 'PZT' and 'copper'</pre>	USPAT; US-PGPUB;	2004/07/01 07:22
		TIMIN and FET and copper	EPO; JPO; DERWENT; IBM TDB	07.22
_	31	<pre>@ad<=19991222 and 'stack capacitor' and 'TiN' and 'PZT' and 'copper'</pre>	USPAT; US-PGPUB; EPO; JPO;	2004/07/01 07:29
_	2	@ad<=19991222 and 'capacitor' and 'TiN' and 'PZT' and 'copper electrode'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 07:33
-	3	@ad<=20010508 and 'capacitor' and 'TiN' and 'PZT' and 'copper electrode'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 07:34
-	283	<pre>@ad<=20010508 and 'capacitor' and 'TiN' and 'PZT' and 'al' with 'electrode'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 07:35
_	77	@ad<=20010508 and 'capacitor' same 'electrode' with 'aluminum' same 'barrier' and 'PZT'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 07:40
	15	<pre>@ad<=20010508 and 'capacitor' same 'electrode' with 'copper' same 'barrier' and 'PZT'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 08:15
	3	@ad<=20010508 and 'electrode' with 'conductive barrier' with 'PZT'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 08:19
_	55	@ad<=20010508 and 'electrode' with 'TiN' with 'PZT'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 08:32
	81	@ad<=20010508 and 'electrode' adj2 'copper' with 'TiN'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 08:33
	5	<pre>@ad<=20010508 and 'copper' with 'electrode' with 'TiN' and 'BST'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 08:45
	3	<pre>@ad<=20010508 and 'copper' with 'electrode' with 'TiN' and 'high k'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 08:45
_	66	@ad<=20010508 and 'copper' with 'electrode' with 'TiN' and 'high dielectric'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 08:48
-	3	<pre>@ad<=20010508 and 'copper' adj2 'electrode' with 'TiN' and 'high dielectric'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 08:49

-	25	<pre>@ad<=19991222 and 'ferroelectric' with</pre>	USPAT;	2004/07/01
		'capacitor' and 'TiAlN' and 'metal layer'	US-PGPUB; EPO; JPO; DERWENT;	11:41
_	0	@ad<=19991222 and 'ferroelectric' with 'capacitor' and 'TiAlN' and 'copper electrode'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 09:02
_	1	"5053917".PN.	IBM_TDB USPAT	2004/07/01 10:37
_	0	<pre>@ad<=19991222 and 'copper' same 'IrO.sub.2' same 'Ir.sub.O.sub3' same 'Ir' and 'ferroelectric'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/01 11:43
	4	@ad<=19991222 and 'copper' same 'IrO.sub.2' same 'Ir' and 'ferroelectric'	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/01 11:43
_	2	@ay<=1999 and tang-shaoping.in.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/01 14:38
_	6	@ay<=1999 and summerfelt-scott.in. and 'ferroelectric'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/02 08:38
	4	<pre>@ay<=1999 and crenshaw-darius.in. and 'ferroelectric'</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/02 08:38
_	1	@ay<=1999 and kirlin-peter.in. and 'ferroelectric'	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/02 08:41
_	5	@ay<=1999 and gnade-bruce.in. and 'ferroelectric'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/02 08:44
	31	<pre>@ay<=1999 and gilbert.in. and 'ferroelectric'</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/02 09:08
_	5	<pre>@ay<=1999 and xing-guoqiang.in. and 'ferroelectric'</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/02 10:59
_	692	@ay<=1999 and 'capacitor' same 'lower electrode' with 'polysilicon'.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/02 09:18
	1	<pre>@ay<=1999 and 'capacitor' same 'lower electrode' with 'polysilicon' same 'copper'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/02 09:19
	9	<pre>@ay<=1999 and 'capacitor' same 'plug' with 'silicon' same 'copper'</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/02 09:24

_	29	@ay<=1999 and 'contact plug' with	USPAT;	2004/07/02
		'silicon' same 'copper'	US-PGPUB;	09:25
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	21	@ay<=1999 and 'contact plug' with	USPAT;	2004/07/02
		'silicon' with 'copper'	US-PGPUB;	09:37
			EPO; JPO;	
			DERWENT;	l
			IBM TDB	
	48	@ay<=1999 and 'capacitor' and 'doped'	USPAT;	2004/07/02
	40	· -	•	1
		adj1 'silicon' with 'copper'	US-PGPUB;	09:38
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	76	@ay<=1999 and 'electrode' and 'doped'	USPAT;	2004/07/02
		adj1 'silicon' with 'copper'	US-PGPUB;	09:38
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	17	@ay<=1999 and 'capacitor' with	USPAT;	2004/07/02
		'electrode' and 'doped' adjl 'silicon'	US-PGPUB;	09:51
		with 'copper'	EPO; JPO;	1
			DERWENT;	
			IBM TDB	
_	33	@ay<=1999 and 'electrode' same 'doped'	USPAT;	2004/07/02
		adj1 'silicon' with 'copper'	US-PGPUB;	09:53
		adji silicon with copper	EPO; JPO;	09:33
			DERWENT;	
			·	
	_	0	IBM_TDB	2004/07/00
_	/	@ay<=1999 and 'capacitor' with	USPAT;	2004/07/02
		'electrode' same 'doped' adj1 'silicon'	US-PGPUB;	09:52
		with 'copper'	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	@ay<=1999 and ma-shawing.in. and	USPAT;	2004/07/02
		'ferroelectric'	US-PGPUB;	11:00
			EPO; JPO;	1
			DERWENT;	1
			IBM TDB	<u> </u>
_	0	@ay<=1999 and ma-shawing.in.	USPAT;	2004/07/02
			US-PGPUB;	11:00
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	1
_	0	ma-shawing.in.	USPAT;	2004/07/02
		ina Dilawing. III.	US-PGPUB;	· · ·
			EPO; JPO;	-1.00
			DERWENT;	1
		0-1000	IBM_TDB	2004/07/00
-	1	@ay<=1999 and ma-shawming.in. and	USPAT;	2004/07/02
		'ferroelectric'	US-PGPUB;	11:01
			EPO; JPO;	
1			DERWENT;	1
			IBM_TDB	
[-	9	ma-shawming.in. and 'ferroelectric'	USPAT;	2004/07/02
			US-PGPUB;	11:01
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	1
_	18	@ad<=20010508 and 'amorphous BST' and	USPAT;	2004/07/02
		'perovskite'	US-PGPUB;	13:07
			EPO; JPO;	"
			DERWENT;	
			IBM TDB	
	<u> </u>	<u></u>	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	